REMARKS

Claims 10-18 are pending in the application. Claims 11, 16, and 17 have been amended, claims 10 and 15 have been canceled, and claims 19 and 20 have been added, leaving claims 11-14 and 16-20 for consideration upon entry of the present Amendment. Applicants respectfully request reconsideration in view of the Amendment.

Claim 15 stands rejected under 35 U.S.C. § 112, first paragraph, as containing subject matter that was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor, at the time the application was filed, had possession of the claimed invention. Claim 15 stands rejected under 35 U.S.C. § 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter that applicant regards as the invention. Claim 15 has been canceled, thereby rendering these rejections moot.

Applicants have added new claims 19 and 20 to further define the invention. Support for those claims can be found at page 2, line 21 to page 3, line 5 and Figures 1 and 2. The Examiner has previously subjected claims 1-18 to a species rejection and Applicants elected claims 10-18. In the restriction requirement, the Examiner stated that there was no generic claim. Applicants note that claim 19 is a generic claim. Thus, if claim 19 is allowed, then Applicants reserve the right to add claims that include the subject matter of claims 1-9, which have previously been canceled without prejudice. Applicants assert that claims 19 and 20 are allowable over Bowers because there is nothing in Bowers that teaches "controlling a charging amount of a parasitic capacitance by changing the input signal." As the Examiner has previously stated, at most, it is inherent that there is a parasitic capacitance in Bowers. Bowers certainly does not teach controlling a charging amount of a parasitic capacitance. Accordingly, Applicants respectfully request that the Examiner allow claims 19 and 20.

Claims 10-14 and 16-18 stand rejected under 35 U.S.C. § 102(b) as being anticipated by Bowers (US 4,675,561). "A claim is anticipated only if each and every element as set forth in the claim is found, either expressly or inherently described, in a single prior art reference." Verdegaal Bros. V. Union Oil Co. of California, 814 F.2d 628, 631, 2 SPQ2d 1051, 1053 (Fed. Cir. 1987). Moreover, "[t]he identical invention must be shown in as complete detail as is contained in the * * claim." Richardson v. Suzuki Motor Co., 868 F.2d 1226, 1236, 9 USPQ2d 1913, 1920 (Fed.

Cir. 1989).

Claim 11 has been rewritten in independent form. Claim 11 includes the following limitation: "an output terminal of said source follower circuit is connected to said island region." The Examiner asserts that Figure 6 of Bowers shows that the output (72) of the source follower circuit (FET2, I2) is connected to the body of FET2. The Examiner asserts that the output (72) of the source follower circuit is connected to the substrate side of the parasitic capacitance. However, claim 11 requires the output terminal is connected to the island region. Bowers does not teach that limitation. Instead, in Bowers, the output terminal is connected to a source region. Thus, Bowers does not anticipate claim 10. In addition, claims 12-14 and 16-18 include all the limitations of claim 11 and thus, Bowers does not anticipate claims 12-14 and 16-18. Applicants respectfully request withdrawal of the rejection as to claims 11-18.

In addition, attached hereto is a marked-up version of the changes made to the application. The attached page is captioned "Version with Markings to Show Changes Made."

In view of the foregoing, it is respectfully submitted that the instant application is in condition for allowance. Accordingly, it is respectfully requested that this application be allowed and a Notice of Allowance issued. If the Examiner believes that a telephone conference with Applicants' attorneys would be advantageous to the disposition of this case, the Examiner is cordially requested to telephone the undersigned. In the event the Commissioner of Patents and Trademarks deems additional fees to be due in connection with this application, Applicants' attorney hereby authorizes that such fee be charged to Deposit Account No. 06-1130.

Respectfully submitted,

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MARKED UP VERSION TO SHOW CHANGES MADE

IN THE CLAIMS:

Please amend claims 11, 16, and 17 in "marked up" format, as follows:

11. (Marked up/Twice Amended) A semiconductor integrated circuit comprising: a pad to which an input signal is externally input:

a source follower circuit including a transistor having a gate connected to said pad and a source for producing an output signal:

wherein a parasitic capacitance is created between said pad and a semiconductor substrate, and said source of the source follower circuit is connected to the semiconductor substrate side of the parasitic capacitance so as to charge and discharge the parasitic capacitance by the output signal of said source follower circuit; The semiconductor integrated circuit defined in Claim 10, further comprising

an island region on the upper surface of said semiconductor substrate containing impurities of a second conductivity type, and a the pad formed on said island region via an oxide film; and wherein said semiconductor substrate contains impurities of a first conductivity type; and wherein an output terminal of said source follower circuit is connected to said island region.

- 16. (Marked up/Amended) The semiconductor integrated circuit defined in Claim 4511, wherein said input stage circuit source follower circuit comprises an amplifier.
- 17. (Marked up/Amended) The semiconductor integrated circuit defined in Claim 1511, wherein said input stagesource follower circuit comprises a field effect transistor integrated on said semiconductor substrate, said field effect transistor having a gate connected to said pad.